



# DATA SHEET

SEMICONDUCTOR

BAS70/A/C/S

## SCHOTTKY DIODE



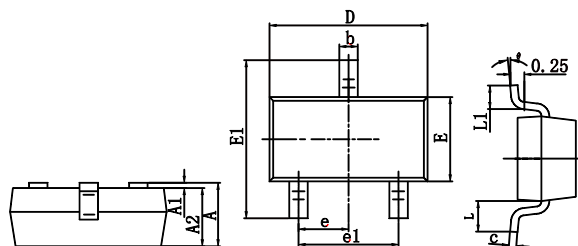
### FEATURES

Low Turn-on voltage  
Fast switching  
Ultra-small surface mount package  
Also available in lead free version

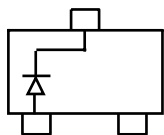
High temperature soldering : 260°C / 10 seconds at terminals  
Pb free product at available : 99% Sn above meet RoHS  
environment substance directive request

SOT23

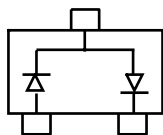
Unit:inch(mm)



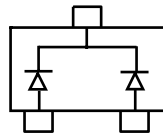
Symbol	Dimensions in Millimeters		Dimensions in Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	6°



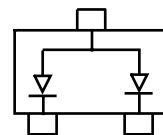
BAS70 Marking: 73



BAS70S Marking: 74



BAS70C Marking: 75



BAS70A Marking: 76

### MAXIMUM RATINGS\* TA=25 unless otherwise noted

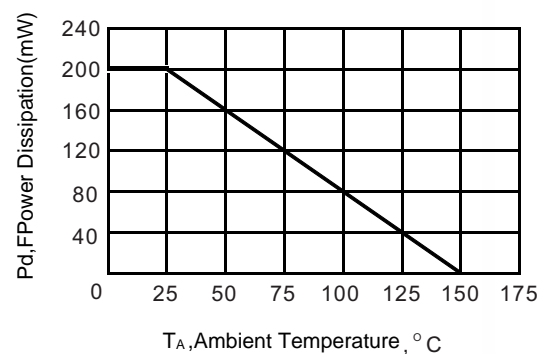
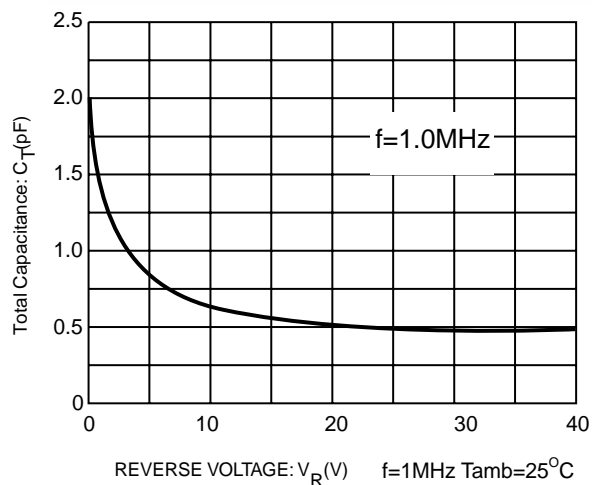
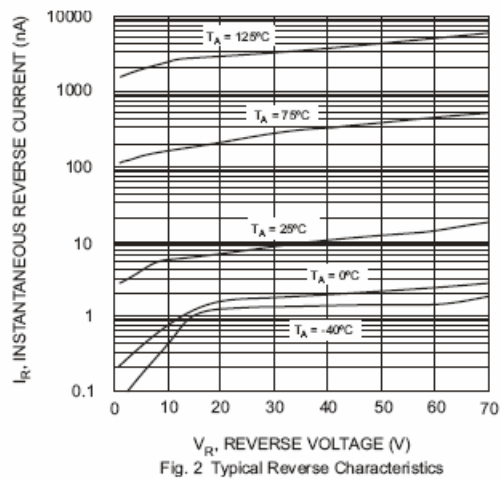
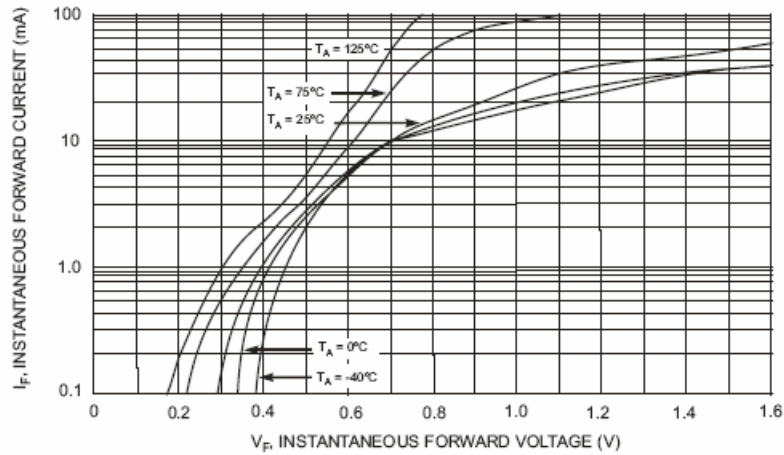
Symbol	Parameter	Value	Units
VR	DC Voltage	70	V
IF	Forward Continuous Current	70	mA
Pd	Power dissipation	200	mW
TJ, Tstg	Junction Operating and Storage Temperature	-55~+150	

### ELECTRICAL CHARACTERISTICS ( Tamb=25 unless otherwise specified )

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	V(BR) R	IR= 10μA	70		V
Reverse voltage leakage current	IR	VR=50V		100	nA
Forward voltage	VF	IF=1mA IF=15mA		410 1000	mV
Diode capacitance	CD	VR=0V f=1MHz		2	pF
Reveres recovery time	trr	IF=IR=10mA,Irr=0.1xIR, RL=100		5	nS

# DEVICE CHARACTERISTICS

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**\* SOLDERING FOOTPRINT**

